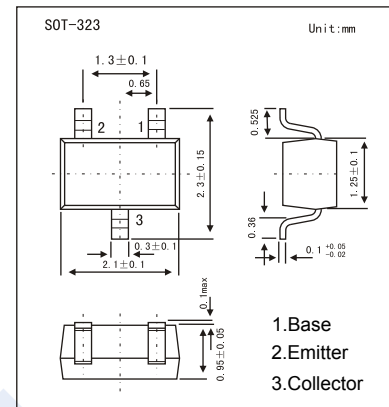


PNP Transistors

2SA1608

■ Features

- High fr : fr=400MHz
- Complementary to 2SC3739



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-60	V
Collector - Emitter Voltage	V _{CE0}	-40	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-500	mA
Collector Power Dissipation	P _C	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E =0	-60			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = -1 mA, I _B =0	-40			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -40 V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -4V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500 mA, I _B =-50 mA		-0.45	-0.75	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-500 mA, I _B =-50 mA		-1	-1.3	
DC current gain (Note.1)	h _{FE(1)}	V _{CE} = -2V, I _C = -150mA	75	140	300	
	h _{FE(2)}	V _{CE} = -2V, I _C = -500mA	20	50		
Turn-on time	t _{on}	V _{CC} =-30V, I _C =-150mA, I _{B1} =-I _{B2} =-15mA		25		ns
Storage time	t _{stg}			70		
Turn-off time	t _{off}			100		
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E =0, f=1MHz		5	8	pF
Transition frequency	f _T	V _{CE} = -10V, I _C = -20mA	150	400		MHz

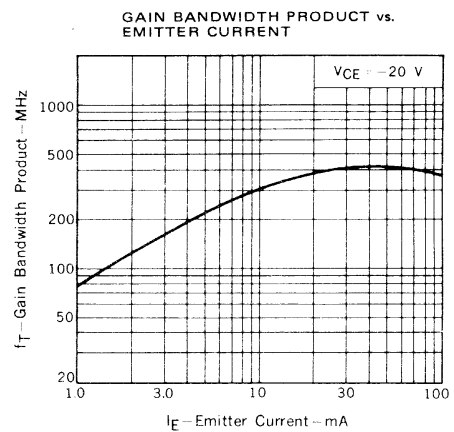
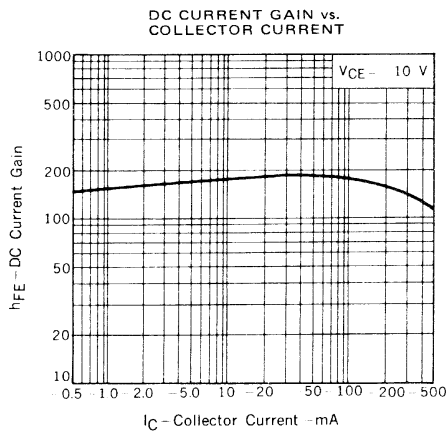
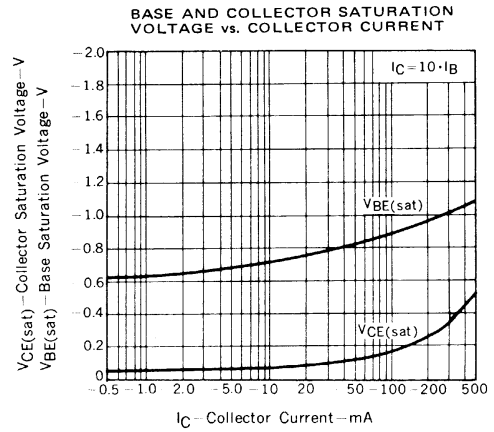
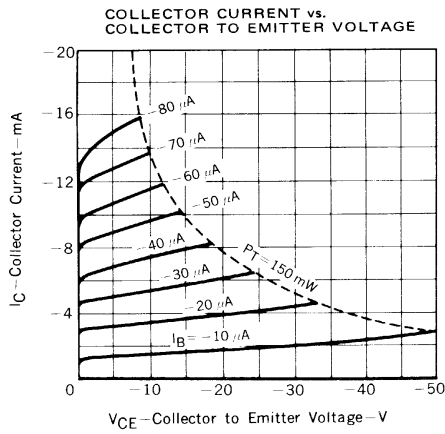
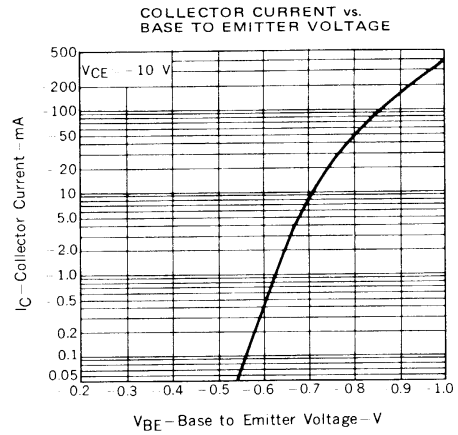
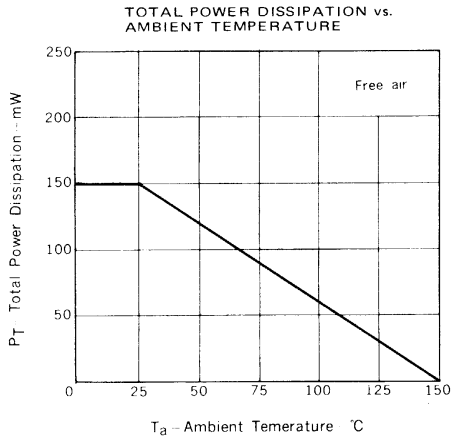
■ Classification of h_{fe} (1)

Type	2SA1608-Y12	2SA1608-Y13	2SA1608-Y14
Range	75-150	100-200	150-300
Marking	Y12	Y13	Y14

PNP Transistors

2SA1608

■ Typical Characteristics



PNP Transistors

2SA1608

■ Typical Characteristics

